

2312-0866-2PCT



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Surler

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF:

KIMIHIRO MATSUSE ET AL.

:EXAMINER: QUACH, T.

SERIAL NO.: 09/530,588

:BATCH NO.:

RCE FILED: HEREWITH

:GROUP ART UNIT: 2814

FOR: WIRING STRUCTURE OF SEMICONDUCTOR DEVICE, ...

AMENDMENT

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

RECEIVED
SEP 21 2001
TECHNOLOGY CENTER 2000

SIR:

In response to the Official Action dated May 22, 2001, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend the claims as shown in clean form below.¹

39. (Amended) The electrode according to claim 37, wherein the gate oxide film is formed of any one of SiO₂, SiOF, Ta₂O₅, and CF_x, where x is an atomic fraction of F from 1 to 4.

B' 40. (Amended) A gate electrode of a transistor formed on a semiconductor substrate, comprising:

a gate oxide film formed between a source and a drain of the transistor;

a barrier metal formed on the gate oxide film; and

a metal layer formed on the barrier metal,

¹The changes being made to the claims are shown using underlining and bracketing to the attachment hereto.